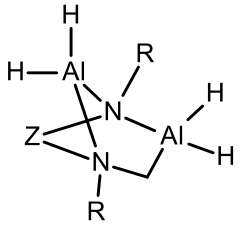
Claims

1. Process for preparing metal-containing films comprising
(a) depositing a metal-containing compound from the gaseous state onto a solid substrate and
(b) bringing the solid substrate with the deposited metal-containing compound in contact with a compound of general formula (I)



(I)

wherein Z is a C_2-C_4 alkylene group, and
R is an alkyl group, an alkenyl group, an aryl group, or a silyl group.

2. The process according to claim 1, wherein R bears no hydrogen atom in the 1-position.

3. The process according to claim 2, wherein R is tert-butyl.

4. The process according to any of the claims 1 to 3, wherein Z is ethylene.

5. The process according to any of the claims 1 to 4, wherein the compound of general formula (I) has a molecular weight of not more than 600 g/mol.

6. The process according to any of the claims 1 to 5, wherein the compound of general formula (I) has a vapor pressure at least 1 mbar at a temperature of 200 °C.

7. The process according to any of the claims 1 to 6, wherein (a) and (b) are successively performed at least twice.

8. The process according to any of the claims 1 to 7, wherein the metal-containing compound contains Ti, Ta, Mn, Mo, W, or Al.

9. The process according to any of the claims 1 to 7, wherein the metal-containing compound is a metal halide.

10. The process according to any of the claims 1 to 9, wherein the temperature does not exceed 350 °C.

11. A compound of general formula (I), wherein Z is a C_2-C_4 alkylene group, and R is an alkyl group, an alkenyl group, an aryl group, or a silyl group.

12. The compound according to claim 11, wherein R bears no hydrogen atom in the 1-position.

13. The compound according to claim 12, wherein R is tert-butyl.

14. The compound according to any of the claims 11 to 13, wherein Z is ethylene.